Supplemental Material for "Antiferroelectric topological insulators in *ABC* compounds"

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NaMgBi under epitaxial strain and hydrostatic pressure

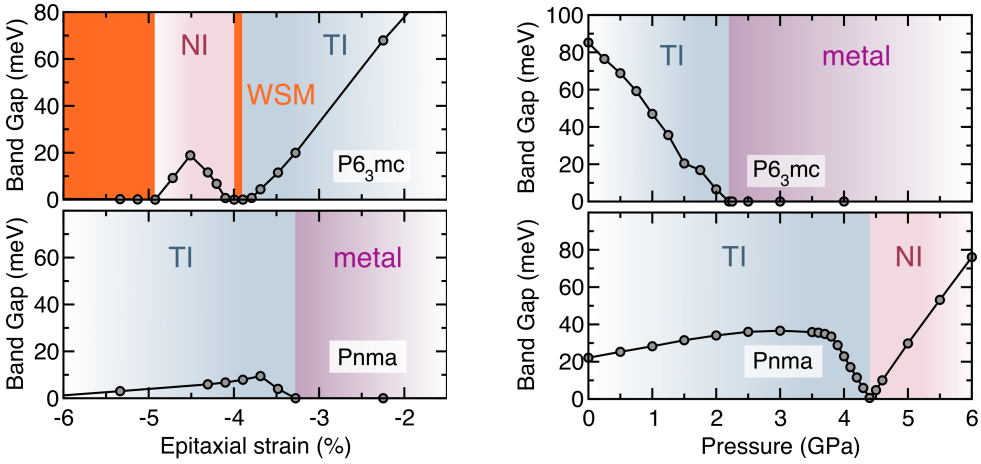

FIG. 1: Band gap of the NaMgBi compounds of polar $P6_3mc$ (top) and antipolar $Pnma$ (bottom) structures as a function of epitaxial strain (left) and hydrostatic pressure (right). The topological character of each phase is also indicated as normal insulator (NI), topological insulator (TI), Weyl semimetal (WSM), or metal.

KMgBi under epitaxial strain and hydrostatic pressure

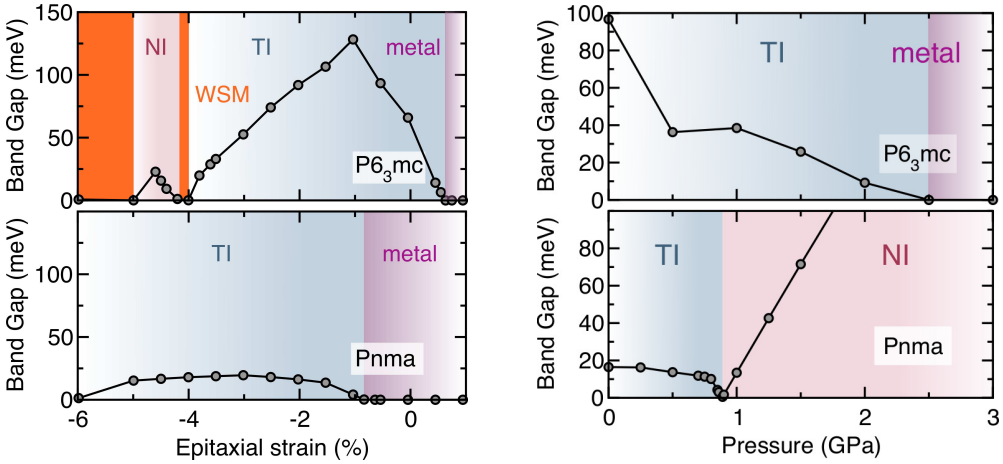

FIG. 2: Band gap of the KMgBi compounds of polar $P6_3mc$ (top) and antipolar $Pnma$ (bottom) structures as a function of epitaxial strain (left) and hydrostatic pressure (right). The topological character of each phase is also indicated as normal insulator (NI), topological insulator (TI), Weyl semimetal (WSM), or metal. The graph of hydrostatic pressure (right) is reproduced from the main manuscript for completeness.